

9097250 TOSHIBA (DISCRETE/OPTO)

99D 16674 D

T-35-25



SEMICONDUCTOR

TECHNICAL DATA

TOSHIBA FIELD EFFECT TRANSISTOR

2SK422

SILICON N CHANNEL MOS TYPE

(π-MOS)

INDUSTRIAL APPLICATIONS

Unit in mm

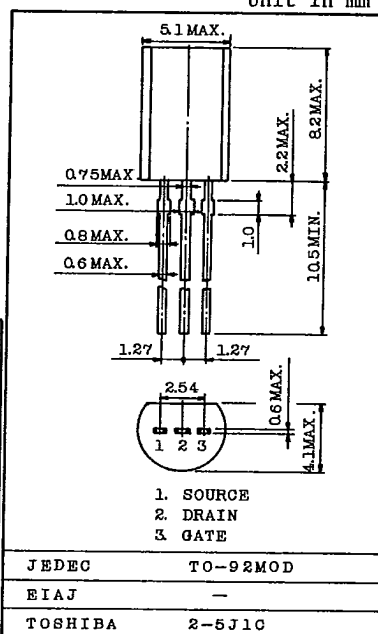
HIGH SPEED SWITCHING APPLICATIONS.
DC-DC CONVERTER AND INTERFACE APPLICATIONS.

FEATURES:

- Excellent Switching Times : $t_{off}=12\text{ns}(\text{Typ.})$
- High Forward Transfer Admittance : $|Y_{fs}|=220\text{mS}(\text{Typ.})$
@ $I_D=0.5\text{A}$
- Low Leakage Current : $I_{GSS}=\pm 100\text{nA}(\text{Max.})$ @ $V_{GS}=\pm 20\text{V}$
 $I_{DSS}=1\text{mA}(\text{Max.})$ @ $V_{DS}=60\text{V}$
- Enhancement-Mode : $V_{th}=1.5\sim 3.5\text{V}$ @ $I_D=1\text{mA}$

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSX}	60	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	0.7	A
	Pulse	I_{DP}	1.0	
Drain Power Dissipation ($T_a=25^\circ\text{C}$)		P_D	900	mW
Channel Temperature		T_{ch}	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	$-55\sim 150$	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS}=\pm 20\text{V}, V_{DS}=0$	-	-	± 100	nA
Drain Cut-off Current		I_{DSS}	$V_{DS}=60\text{V}, V_{GS}=0$	-	-	1.0	mA
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$I_D=10\text{mA}, V_{GS}=0$	60	-	-	V
Gate Threshold Voltage		V_{th}	$V_{DS}=10\text{V}, I_D=1\text{mA}$	1.5	-	3.5	V
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS}=10\text{V}, I_D=0.5\text{A}$	80	220	-	nS
Drain-Source ON Resistance		$R_{DS(ON)}$	$I_D=0.5\text{A}, V_{GS}=10\text{V}$	-	1.4	2.8	Ω
Drain-Source ON Voltage		$V_{DS(ON)}$	$I_D=1\text{A}, V_{GS}=10\text{V}$	-	2	4	V
Input Capacitance		C_{iss}	$V_{DS}=10\text{V}, V_{GS}=0, f=1\text{MHz}$	-	45	70	pF
Reverse Transfer Capacitance		C_{rss}	$V_{DS}=10\text{V}, V_{GS}=0, f=1\text{MHz}$	-	20	35	pF
Output Capacitance		C_{oss}	$V_{DS}=10\text{V}, V_{GS}=0, f=1\text{MHz}$	-	60	100	pF
Switching Time	Rise Time	t_r		-	11	20	ns
	Turn-on Time	t_{on}		-	17	35	
	Fall Time	t_f		-	6	10	
	Turn-off Time	t_{off}		-	12	25	

THIS TRANSISTOR IS THE ELECTROSTATIC SENSITIVE DEVICE. PLEASE HANDLE WITH CAUTION.

TOSHIBA CORPORATION

GT1A2

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99D 16675

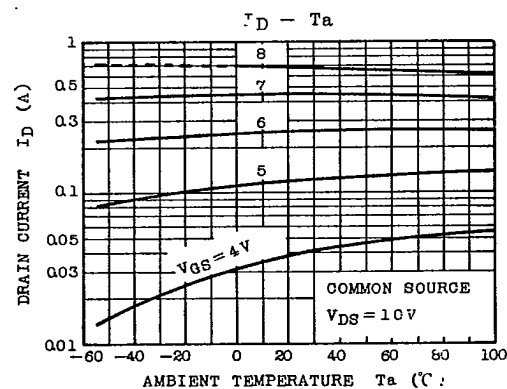
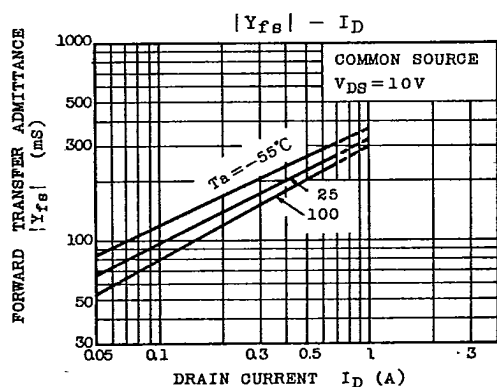
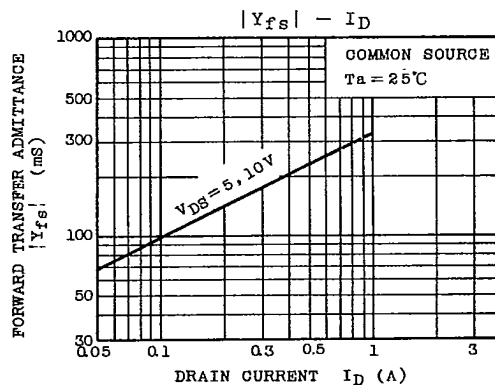
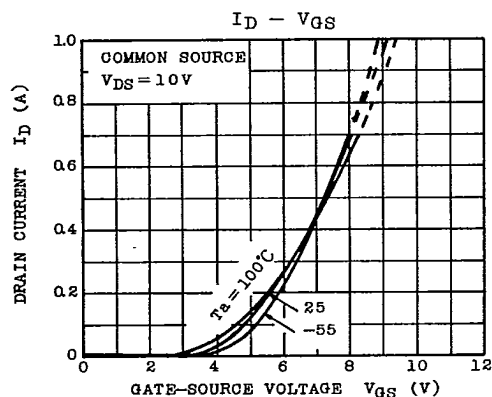
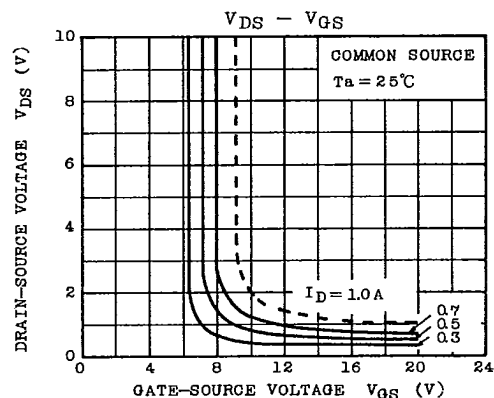
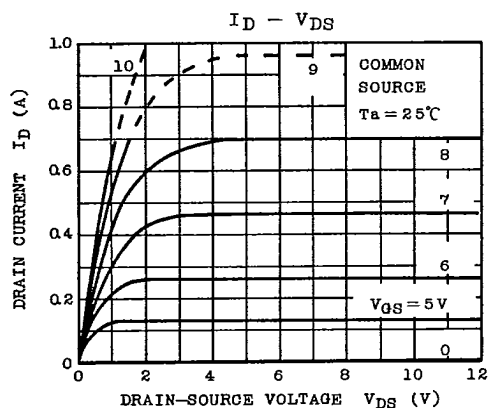
DT-35-25



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TOSHIBA CORPORATION

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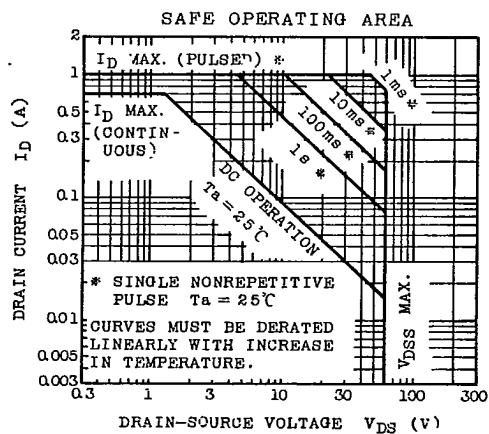
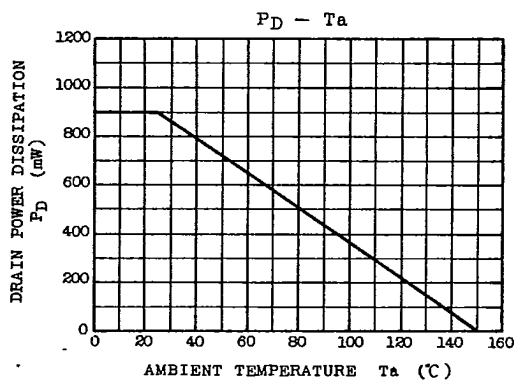
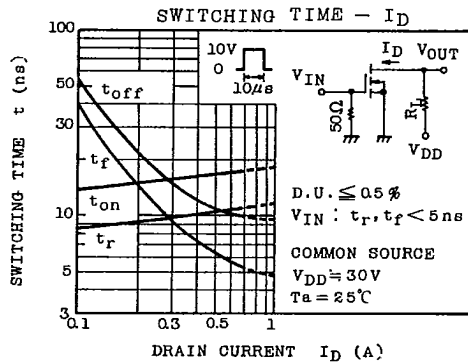
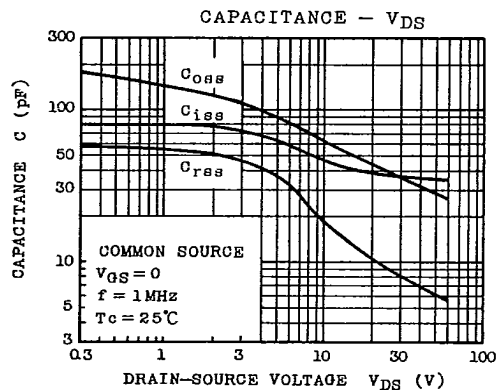
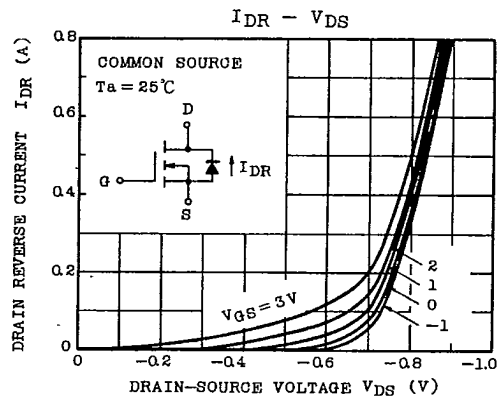
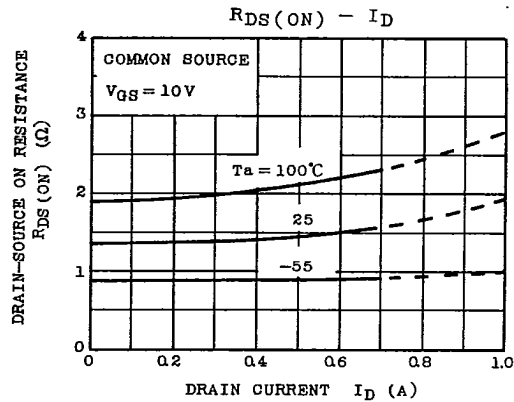
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